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December 2013

SGH10N60RUFD 600V, 10 A Short Circuit Rated IGBT

Features

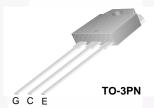
- Short Circuit Rated 10 us @ T_C = 100°C, V_{GE} = 15 V
- · High Speed Switching
- Low Saturation Voltage : $V_{CE(sat)} = 2.2 \text{ V} @ I_C = 10 \text{ A}$
- · High Input Impedance
- CO-PAK, IGBT with FRD : t_{rr} = 42 ns (typ.)

Description

Fairchild's RUFD series of insulated gate bipolar transistors (IGBTs) provide low conduction and switching losses as well as short circuit ruggedness. The RUFD series is designed for applications such as motor control, uninterrupted power supplies (UPS) and general inverters where short circuit ruggedness is a required feature.

Applications

AC & DC Motors Controls, General Purpose Inverters, and Robotics, and Servo Controls





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Description		Ratings	Unit
V _{CES}	Collector-Emitter Voltage		600	V
V _{GES}	Gate-Emitter Voltage		± 20	V
	Collector Current	@ $T_C = 25^{\circ}C$	16	A
I _C	Collector Current	@ T _C = 100°C	10	A
I _{CM (1)}	Pulsed Collector Current		30	A
l _F	Diode Continuous Forward Current	@ T _C = 100°C	12	A
I _{FM}	Diode Maximum Forward Current		92	A
T _{SC}	Short Circuit Withstand Time	@ T _C = 100°C	10	us
P_{D}	Maximum Power Dissipation	@ $T_C = 25^{\circ}C$	75	W
	Maximum Power Dissipation	@ T _C = 100°C	30	W
T _J	Operating Junction Temperature	-	-55 to +150	°C
T _{stg}	Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds		300	°C

Notes :

(1) Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction-to-Case		1.6	°C/W
$R_{\theta JC}(DIODE)$	Thermal Resistance, Junction-to-Case		2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		40	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
SGH10N60RUFD	SGH10N60RUFD	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics of the IGBT $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	racteristics					
BV _{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V, } I_{C} = 250 \text{ uA}$	600			V
ΔB _{VCES} / ΔT _J	Temperature Coefficient of Breakdown Voltage	V _{GE} = 0 V, I _C = 1 mA		0.6		V/°C
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0 V$			250	uA
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$			± 100	nA
On Chai	racteristics					
V _{GE(th)}	G-E Threshold Voltage	$I_C = 10 \text{ mA}, V_{CE} = V_{GE}$	5.0	6.0	8.5	V
	Collector to Emitter	$I_C = 10 \text{ A}, V_{GE} = 15 \text{ V}$		2.2	2.8	V
V _{CE(sat)}	Saturation Voltage	I _C = 16 A, V _{GE} = 15 V		2.5		V
Dynami	c Characteristics			1		
C _{ies}	Input Capacitance	V 20 V V 0 V		660		pF
C _{oes}	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1 MHz		115		pF
C _{res}	Reverse Transfer Capacitance	1 = 1 1011 12		25		pF
	ng Characteristics			15		
t _{d(on)}	Turn-On Delay Time			15		ns
t _r	Rise Time	-		30		ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 300 \text{ V}, I_C = 10 \text{ A},$		36	50	ns
t _f	Fall Time	$R_G = 20 \Omega$, $V_{GE} = 15 V$,		158	200	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 25°C		141		uJ
E _{off}	Turn-Off Switching Loss	-		215		uJ
E _{ts}	Total Switching Loss			356	500	uJ
t _{d(on)}	Turn-On Delay Time	-		16 33		ns
t _r	Rise Time Turn-Off Delay Time			42	60	ns ns
t _{d(off)}	Fall Time	$V_{CC} = 300 \text{ V}, I_{C} = 10 \text{ A},$ $R_{G} = 20\Omega, V_{GE} = 15 \text{ V},$		242	350	ns
E _{on}	Turn-On Switching Loss	Inductive Load, $T_C = 125^{\circ}C$		161		uJ
E _{off}	Turn-Off Switching Loss			452		uJ
E _{ts}	Total Switching Loss			613	860	uJ
T _{sc}	Short Circuit Withstand Time	V _{CC} = 300 V, V _{GE} = 15 V @ T _C = 100°C	10			us
Qq	Total Gate Charge			30	45	nC
Q _{ge}	Gate-Emitter Charge	$V_{CE} = 300 \text{ V}, I_{C} = 10 \text{ A},$		5	10	nC
Q _{gc}	Gate-Collector Charge	V _{GE} = 15 V		8	16	nC
L _e	Internal Emitter Inductance	Measured 5mm from PKG		14		nH

Electrical Characteristics of DIODE $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
V_{FM}	Diode Forward Voltage	I _C = 12 Δ	$T_C = 25^{\circ}C$		1.4	1.7	V
			T _C = 100°C		1.3		
	t _{rr} Diode Reverse Recovery Time		$T_C = 25^{\circ}C$		42	60	20
^l rr		I _F = 12 A,	T _C = 100°C		60		ns
	Diode Peak Reverse Recovery		$T_C = 25^{\circ}C$		3.5	6.0	Α
¹rr	Current	di/dt = 200 A/us	T _C = 100°C		5.6		A
0	Q _{rr} Diode Reverse Recovery Charge		$T_C = 25^{\circ}C$		80	180	nC
Q _{rr}			T _C = 100°C		220		110

Typical Characteristics

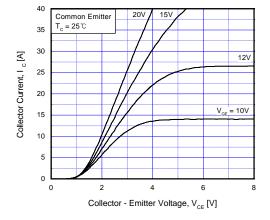


Fig 1. Typical Output Characteristics

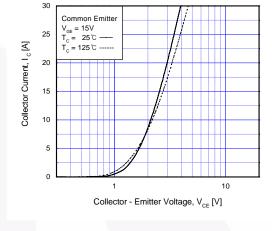


Fig 3. Saturation Voltage vs. Case
Temperature at Variant Current Level

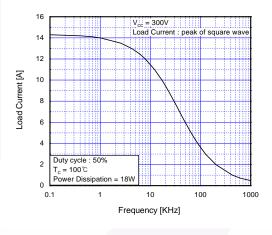


Fig 4. Load Current vs. Frequency

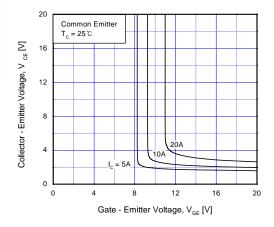


Fig 5. Saturation Voltage vs. V_{GE}

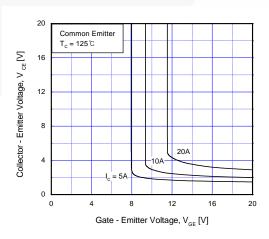


Fig 6. Saturation Voltage vs. V_{GE}

Typical Characteristics (continued)

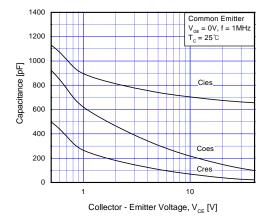
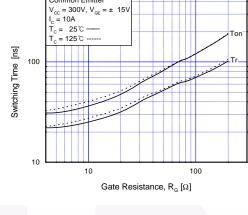


Fig 7. Capacitance Characteristics



Common Emitter

Fig 8. Turn-On Characteristics vs.
Gate Resistance

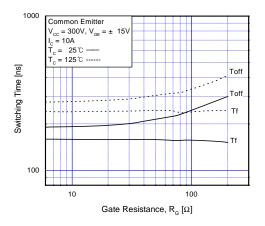


Fig 9. Turn-Off Characteristics vs.

Gate Resistance

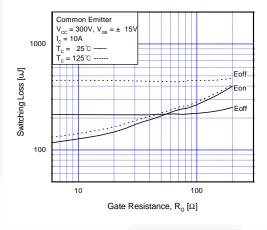


Fig 10. Switching Loss vs. Gate Resistance

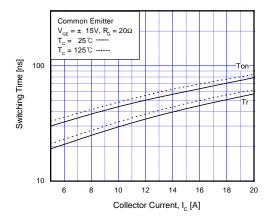


Fig 11. Turn-On Characteristics vs. Collector Current

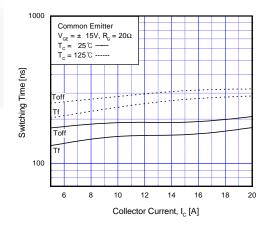


Fig 12. Turn-Off Characteristics vs. Collector Current

Typical Characteristics (continued)

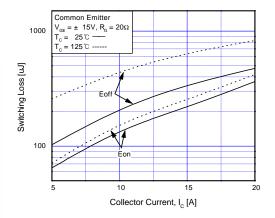


Fig 13. Switching Loss vs. Collector Current

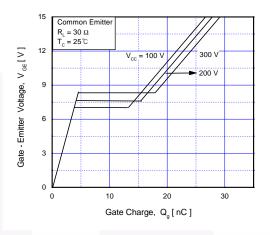


Fig 14. Gate Charge Characteristics

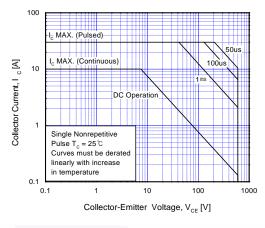


Fig 15. SOA Characteristics

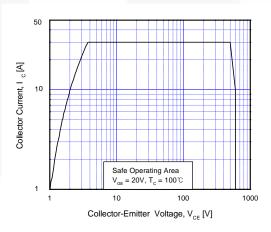


Fig 16. Turn-Off SOA Characteristics

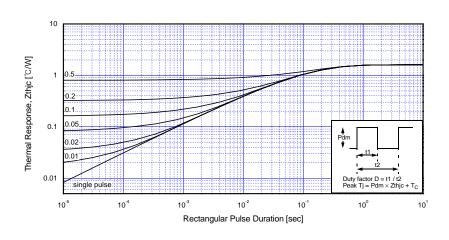


Fig 17. Transient Thermal Impedance of IGBT

Typical Characteristics (continued)

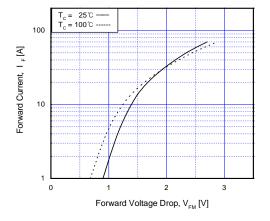


Fig 18. Forward Characteristics

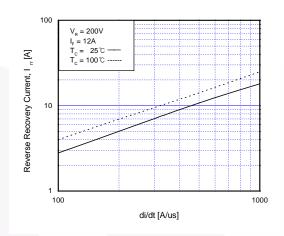


Fig 19. Reverse Recovery Current

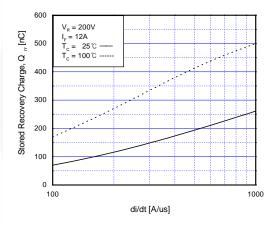


Fig 20. Stored Charge

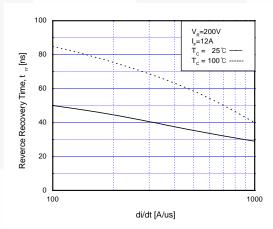
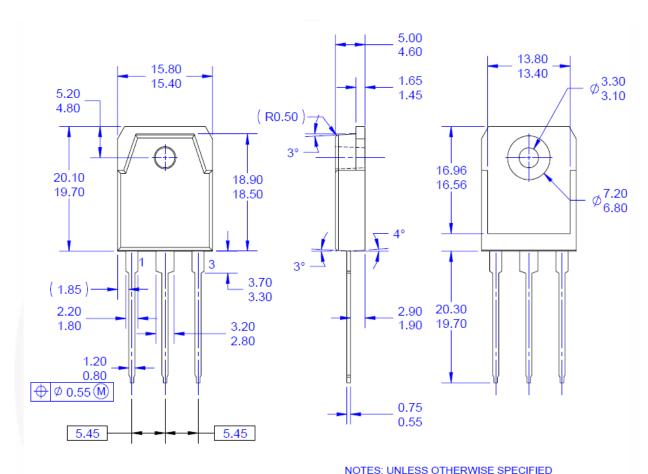


Fig 21. Reverse Recovery Time

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A) THIS PACKAGE CONFORMS TO EIAJ

- SC-65 PACKAGING STANDARD. ALL DIMENSIONS ARE IN MILLIMETERS. (R0.50) C) DIMENSION AND TOLERANCING PER ASME14.5
 - D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
 E) THIS PACKAGE IS INTENDED ONLY FOR TO3PN.

 - F) DRAWING FILE NAME: TO3P03AREV4.

Figure 22. TO3, 3-Lead, Plastic, EIAJ SC-65

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